74AUP1G00

Low-power 2-input NAND gate

Rev. 10 — 19 September 2024

Product data sheet

1. General description

The 74AUP1G00 is a single 2-input NAND gate. Schmitt-trigger action at all inputs makes the circuit tolerant of slower input rise and fall times. This device ensures very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V. This device is fully specified for partial power down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- CMOS low power dissipation
- High noise immunity
- · Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.65 V to 1.95 V)
 - JESD8-5 (2.3 V to 2.7 V)
 - JESD8C (2.7 V to 3.6 V)
- Low static power consumption; I_{CC} = 0.9 μA (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Overvoltage tolerant inputs to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- · Multiple package options
- ESD protection:
 - HBM: ANSI/ESDA/JEDEC JS-001 class 3A exceeds 5000 V
 - CDM: ANSI/ESDA/JEDEC JS-002 class C3 exceeds 1000 V
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



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3. Ordering information

Table 1. Ordering information

Type number	Package	Package						
	Temperature range	Name	Description	Version				
74AUP1G00GW	-40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1				
74AUP1G00GM	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	<u>SOT886</u>				
74AUP1G00GN	-40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 0.9 × 1.0 × 0.35 mm	<u>SOT1115</u>				
74AUP1G00GS	-40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 1.0 × 1.0 × 0.35 mm	SOT1202				
74AUP1G00GX	-40 °C to +125 °C	X2SON5	plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body 0.8 × 0.8 × 0.32 mm	SOT1226-3				
74AUP1G00GZ	-40 °C to +125 °C	XSON5	plastic thermal enhanced extremely thin small outline package with side-wettable flanks (SWF); no leads; 5 terminals; body 1.1 × 0.85 × 0.5 mm	SOT8065-1				

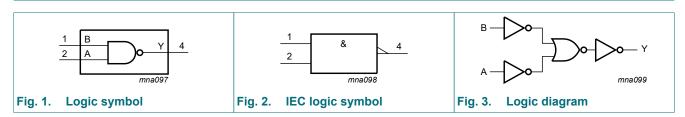
4. Marking

Table 2. Marking

Table 21 Marking						
Marking code [1]						
рА						
рА						
pA						
рА						
рА						
рА						

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

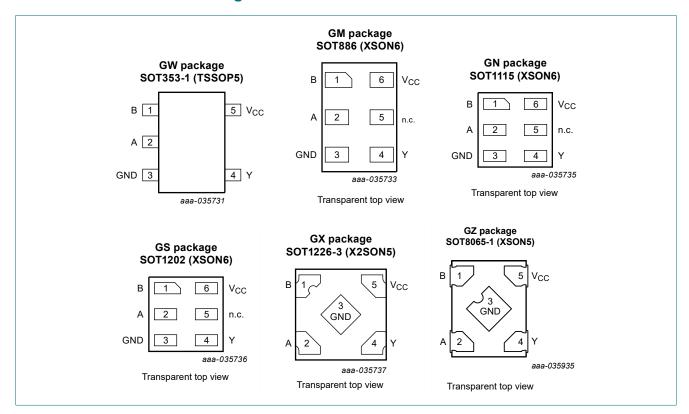
5. Functional diagram



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6. Pinning information

6.1. Pinning



6.2. Pin description

Table 3. Pin description

Symbol	Pin	Description		
	TSSOP5, X2SON5 and XSON5	XSON6		
В	1	1	data input	
A	2	2	data input	
GND	3	3	ground (0 V)	
Υ	4	4	data output	
n.c.	-	5	not connected	
V _{CC}	5	6	supply voltage	

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7. Functional description

Table 4. Function table

 $H = HIGH \ voltage \ level; \ L = LOW \ voltage \ level.$

Input		Output
A	В	Υ
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage	[1]	-0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode [1]	-0.5	V _{CC} + 0.5	V
		Power-down mode; V _{CC} = 0 V [1]	-0.5	+4.6	V
I _O	output current	$V_O = 0 V \text{ to } V_{CC}$	-	±20	mA
I _{CC}	supply current		-	+50	mA
I_{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$ [2]	-	250	mW

^[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V _{CC}	V
		Power-down mode; V _{CC} = 0 V	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 0.8 V to 3.6 V	0	200	ns/V

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^[2] For SOT353-1 (TSSOP5) package: Ptot derates linearly with 3.3 mW/K above 74 °C.

For SOT886 (XSON6) package: P_{tot} derates linearly with 3.3 mW/K above 74 $^{\circ}\text{C}.$

For SOT1115 (XSON6) package: Ptot derates linearly with 3.2 mW/K above 71 °C.

For SOT1202 (XSON6) package: Ptot derates linearly with 3.3 mW/K above 74 °C.

For SOT1226-3 (X2SON5) package: Ptot derates linearly with 3.0 mW/K above 67 °C.

For SOT8065-1 (XSON5) package: Ptot derates linearly with 3.2 mW/K above 72 °C.

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10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	25 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.70×V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65×V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30×V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35×V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I _O = -20 μA; V _{CC} = 0.8 V to 3.6 V	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.75×V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.11	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.32	-	-	V
		I_{O} = -2.3 mA; V_{CC} = 2.3 V	2.05	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.9	-	-	V
		I_{O} = -2.7 mA; V_{CC} = 3.0 V	2.72	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.6	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3×V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.31	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.44	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.31	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.44	V
I _I	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.1	μΑ
I _{OFF}	power-off leakage current	V_{I} or $V_{O} = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.2	μA
Δl _{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.2	μA
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	0.5	μA
ΔI _{CC}	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$ [1]	-	-	40	μΑ
Cı	input capacitance	V_{CC} = 0 V to 3.6 V; V_{I} = GND or V_{CC}	-	0.8	-	pF
Co	output capacitance	V _O = GND; V _{CC} = 0 V	-	1.7	-	pF

Symbo	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} =	-40 °C to +85 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.70×V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65×V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30×V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35×V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_{O} = -20 μ A; V_{CC} = 0.8 V to 3.6 V	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.7×V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.03	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.30	-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	1.97	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.85	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.67	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.55	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3×V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.37	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.35	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.33	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.45	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.33	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.45	V
l _l	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.5	μA
I _{OFF}	power-off leakage current	V_{I} or $V_{O} = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.5	μA
ΔI _{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.6	μΑ
I _{CC}	supply current	V_{I} = GND or V_{CC} ; I_{O} = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	0.9	μΑ
ΔI _{CC}	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$ [1] -	-	50	μA
T _{amb} =	-40 °C to +125 °C				'	
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.75×V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.70×V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.25×V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.30×V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	_	-	0.9	V

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I _O = -20 μA; V _{CC} = 0.8 V to 3.6 V	V _{CC} - 0.11	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.6×V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	0.93	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.17	-	-	V
		I_{O} = -2.3 mA; V_{CC} = 2.3 V	1.77	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.67	-	-	V
		I_{O} = -2.7 mA; V_{CC} = 3.0 V	2.40	-	-	V
		I_{O} = -4.0 mA; V_{CC} = 3.0 V	2.30	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.33×V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.41	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.39	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.36	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.50	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.36	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.50	V
I _I	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.75	μΑ
I _{OFF}	power-off leakage current	V_{I} or $V_{O} = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.75	μΑ
Δl _{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.75	μΑ
I _{CC}	supply current	V_I = GND or V_{CC} ; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	1.4	μΑ
ΔI_{CC}	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$ [1]	-	-	75	μΑ

^[1] One input at V_{CC} - 0.6 V, other input at V_{CC} or GND.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 5

Symbol	Parameter	Conditions	Min	Typ [1]	Max	Unit				
T _{amb} = 2	T _{amb} = 25 °C; C _L = 5 pF									
t _{pd}	propagation delay	A, B to Y; see <u>Fig. 4</u> [2]								
		V _{CC} = 0.8 V	-	17.5	-	ns				
		V _{CC} = 1.1 V to 1.3 V	2.5	5.3	11.0	ns				
		V _{CC} = 1.4 V to 1.6 V	2.0	3.8	6.8	ns				
		V _{CC} = 1.65 V to 1.95 V	1.6	3.1	5.3	ns				
		V _{CC} = 2.3 V to 2.7 V	1.3	2.5	4.0	ns				
		V _{CC} = 3.0 V to 3.6 V	1.0	2.2	3.6	ns				

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Symbol	Parameter	Conditions		Min	Typ [1]	Max	Unit
T _{amb} = 2	25 °C; C _L = 10 pF						'
t _{pd}	propagation delay	A, B to Y; see Fig. 4	[2]				
		V _{CC} = 0.8 V		-	21.0	-	ns
		V _{CC} = 1.1 V to 1.3 V		2.4	6.1	13.0	ns
		V _{CC} = 1.4 V to 1.6 V		2.4	4.4	7.9	ns
		V _{CC} = 1.65 V to 1.95 V		2.0	3.7	6.2	ns
		V _{CC} = 2.3 V to 2.7 V		1.4	3.0	4.7	ns
		V _{CC} = 3.0 V to 3.6 V		1.3	2.8	4.3	ns
T _{amb} = 2	25 °C; C _L = 15 pF						'
t _{pd}	propagation delay	A, B to Y; see Fig. 4	[2]				
		V _{CC} = 0.8 V		-	24.5	-	ns
		V _{CC} = 1.1 V to 1.3 V		3.4	6.9	14.8	ns
		V _{CC} = 1.4 V to 1.6 V		2.8	5.0	8.9	ns
		V _{CC} = 1.65 V to 1.95 V		2.0	4.1	7.0	ns
		V _{CC} = 2.3 V to 2.7 V		1.7	3.5	5.3	ns
		V _{CC} = 3.0 V to 3.6 V		1.6	3.2	4.9	ns
T _{amb} = 2	25 °C; C _L = 30 pF	,					'
t _{pd}	propagation delay	A, B to Y; see Fig. 4	[2]				
		V _{CC} = 0.8 V		-	34.8	-	ns
		V _{CC} = 1.1 V to 1.3 V		4.6	9.2	20.1	ns
		V _{CC} = 1.4 V to 1.6 V		3.0	6.5	11.8	ns
		V _{CC} = 1.65 V to 1.95 V		2.6	5.4	9.3	ns
		V _{CC} = 2.3 V to 2.7 V		2.4	4.6	7.1	ns
		V _{CC} = 3.0 V to 3.6 V		2.3	4.3	6.5	ns
T _{amb} = 2	25 °C						'
C _{PD}	power dissipation	$f = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$	[3]				
	capacitance	V _{CC} = 0.8 V		-	2.6	-	pF
		V _{CC} = 1.1 V to 1.3 V		-	2.8	-	pF
		V _{CC} = 1.4 V to 1.6 V		-	2.9	-	pF
		V _{CC} = 1.65 V to 1.95 V		-	3.1	-	pF
		V _{CC} = 2.3 V to 2.7 V		-	3.6	-	pF
		V _{CC} = 3.0 V to 3.6 V		-	4.2	-	pF

^[1] All typical values are measured at nominal V_{CC} .

f_i = input frequency in MHz;

 f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

 ^[2] t_{pd} is the same as t_{PLH} and t_{PHL}.
 [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 P_D = C_{PD} × V_{CC}² × f_i × N + Σ(C_L × V_{CC}² × f_o) where:

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Table 9. Dynamic characteristics

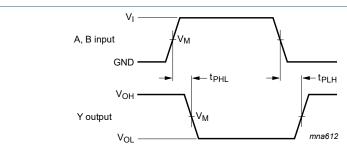
Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 5

Symbol	Parameter	Conditions	-40 °C t	-40 °C to +85 °C		-40 °C to +125 °C	
			Min	Max	Min	Max	
C _L = 5 p	F						
t _{pd}	propagation delay	A, B to Y; see <u>Fig. 4</u> [1]					
		V _{CC} = 1.1 V to 1.3 V	2.1	12.2	2.1	13.5	ns
		V _{CC} = 1.4 V to 1.6 V	1.8	7.8	1.8	8.6	ns
		V _{CC} = 1.65 V to 1.95 V	1.4	6.2	1.4	6.9	ns
		V _{CC} = 2.3 V to 2.7 V	1.1	4.7	1.1	5.2	ns
		V _{CC} = 3.0 V to 3.6 V	1.0	4.2	1.0	4.7	ns
C _L = 10	pF						
t _{pd}	propagation delay	A, B to Y; see <u>Fig. 4</u> [1]					
		V _{CC} = 1.1 V to 1.3 V	2.2	14.4	2.2	15.9	ns
		V _{CC} = 1.4 V to 1.6 V	2.2	9.2	2.2	10.2	ns
		V _{CC} = 1.65 V to 1.95 V	1.9	7.3	1.9	8.1	ns
		V _{CC} = 2.3 V to 2.7 V	1.3	5.6	1.3	6.2	ns
		V _{CC} = 3.0 V to 3.6 V	1.2	4.9	1.2	5.4	ns
C _L = 15	pF						
t _{pd}	propagation delay	A, B to Y; see <u>Fig. 4</u> [1]					
		V _{CC} = 1.1 V to 1.3 V	3.1	16.5	3.1	18.2	ns
		V _{CC} = 1.4 V to 1.6 V	2.5	10.5	2.5	11.6	ns
		V _{CC} = 1.65 V to 1.95 V	2.0	8.3	2.0	9.2	ns
		V _{CC} = 2.3 V to 2.7 V	1.5	6.4	1.5	7.1	ns
		V _{CC} = 3.0 V to 3.6 V	1.4	5.7	1.4	6.3	ns
C _L = 30	pF						
t _{pd}	propagation delay	A, B to Y; see <u>Fig. 4</u> [1]					
		V _{CC} = 1.1 V to 1.3 V	4.1	22.6	4.1	24.9	ns
		V _{CC} = 1.4 V to 1.6 V	2.9	14.0	2.9	15.4	ns
		V _{CC} = 1.65 V to 1.95 V	2.3	11.1	2.3	12.3	ns
		V _{CC} = 2.3 V to 2.7 V	2.1	8.5	2.1	9.4	ns
		V _{CC} = 3.0 V to 3.6 V	2.1	7.6	2.1	8.4	ns

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

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11.1. Waveforms and test circuit



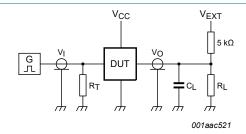
Measurement points are given in Table 10.

Logic levels: V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig. 4. The data input (A or B) to output (Y) propagation delays

Table 10. Measurement points

Supply voltage	Input			Output
V _{CC}	V _M	V _I	$t_r = t_f$	V _M
0.8 V to 3.6 V	0.5 × V _{CC}	V _{CC}	≤ 3.0 ns	0.5 × V _{CC}



Test data is given in Table 11.

Definitions for test circuit:

R_L = Load resistance;

C_L = Load capacitance including jig and probe capacitance;

 R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator;

 V_{EXT} = External voltage for measuring switching times.

Fig. 5. Test circuit for measuring switching times

Table 11. Test data

Supply voltage	Load		V _{EXT}		
V _{CC}	C _L	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	2 × V _{CC}

[1] For measuring enable and disable times $R_L = 5 \text{ k}\Omega$. For measuring propagation delays, setup and hold times and pulse width $R_L = 1 \text{ M}\Omega$.

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12. Package outline

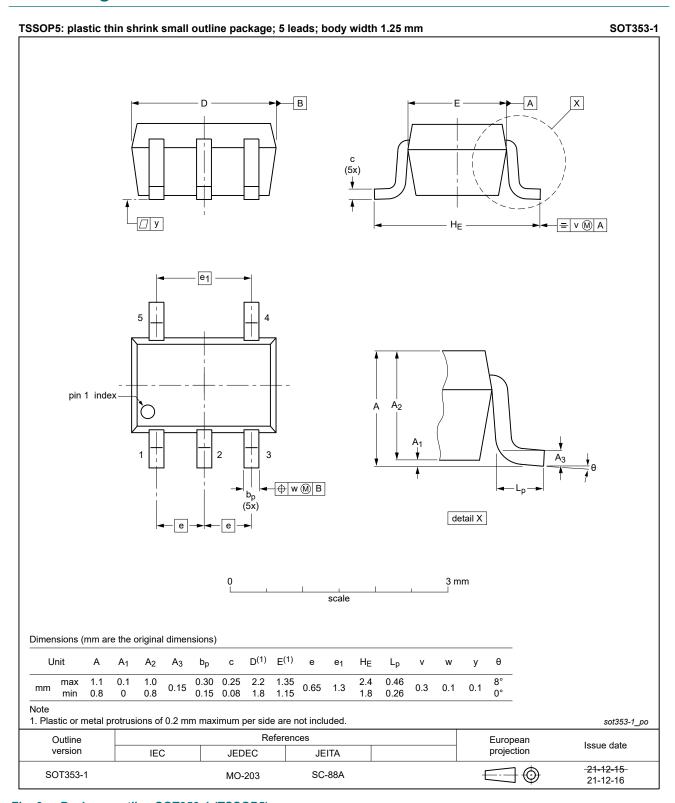


Fig. 6. Package outline SOT353-1 (TSSOP5)

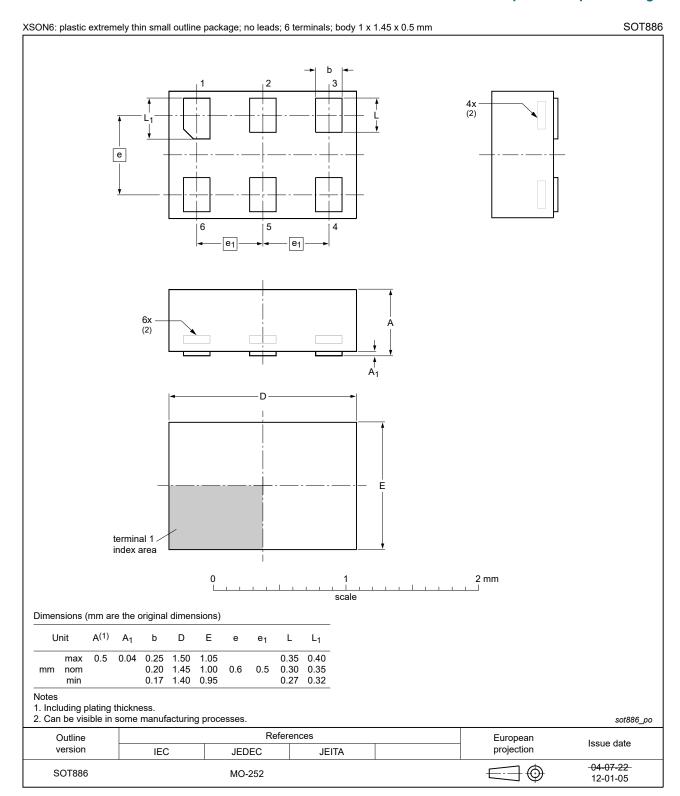


Fig. 7. Package outline SOT886 (XSON6)

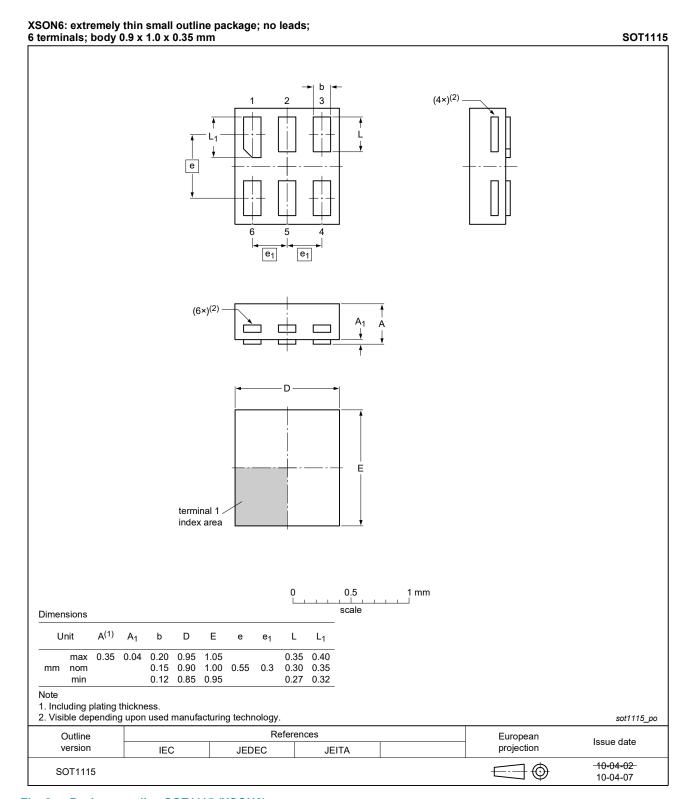


Fig. 8. Package outline SOT1115 (XSON6)

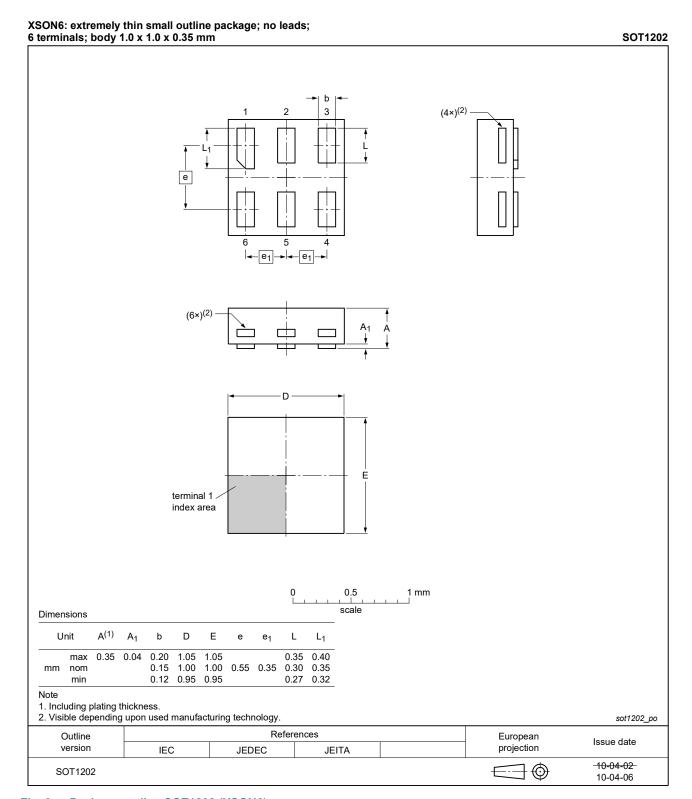


Fig. 9. Package outline SOT1202 (XSON6)

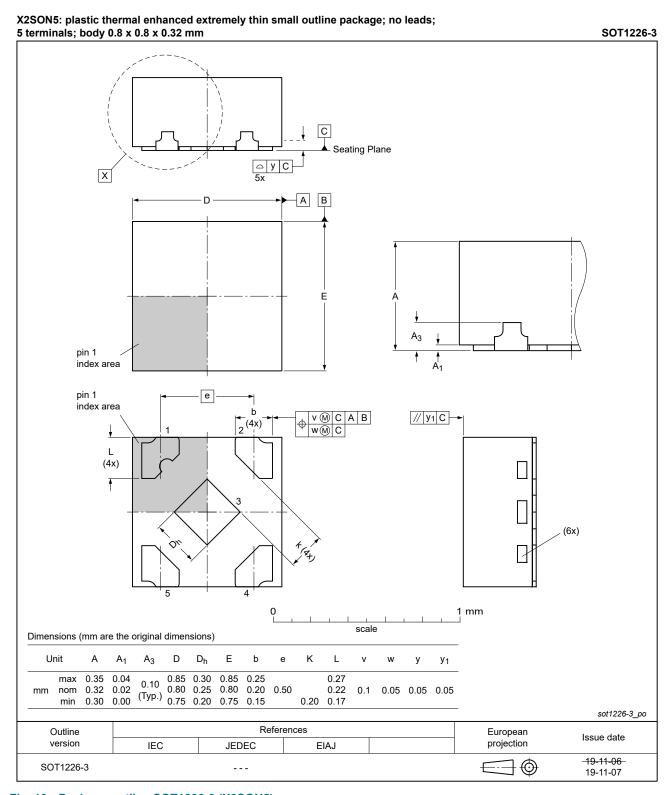


Fig. 10. Package outline SOT1226-3 (X2SON5)

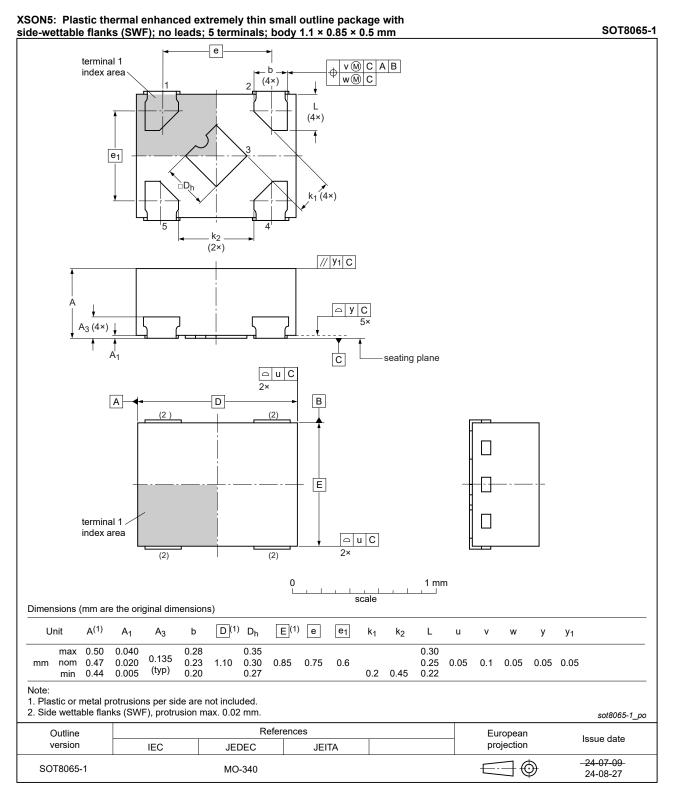


Fig. 11. Package outline SOT8065-1 (XSON5)

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13. Abbreviations

Table 12. Abbreviations

Acronym	Description
ANSI	American National Standards Institute
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
ESDA	ElectroStatic Discharge Association
НВМ	Human Body Model
JEDEC	Joint Electron Device Engineering Council

14. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
74AUP1G00 v.10	20240919	Product data sheet	-	74AUP1G00 v.9.1		
Modifications:	Type numbe	Type number 74AUP1G00GZ (SOT8065-1/XSON5) added.				
74AUP1G00 v.9.1	20230711	Product data sheet	-	74AUP1G00 v.8		
Modifications:	Section 2: E	<u>Section 2</u> : ESD specification updated according to the latest JEDEC standard.				
74AUP1G00 v.8	20220113	Product data sheet	-	74AUP1G00 v.7		
Modifications:	<u>Table 5</u>: DerType numbeSOT1226 (X	Type named 7 intel 166661 (661661) tellioved.				
74AUP1G00 v.7	20190423	Product data sheet	-	74AUP1G00 v.6		
Modifications:	of Nexperia. • Legal texts h	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Pin configuration drawing SOT1226 (X2SON5) updated. 				
74AUP1G00 v.6	20120627	Product data sheet	-	74AUP1G00 v.5		
Modifications:	Added type	Added type number 74AUP1G00GX (SOT1226).				
74AUP1G00 v.5	20120316	Product data sheet	-	74AUP1G00 v.4		
Modifications:	Package out	Package outline drawing of SOT886 (<u>Fig. 7</u>) modified.				
74AUP1G00 v.4	20111115	Product data sheet	-	74AUP1G00 v.3		
Modifications:	 Legal pages 	Legal pages updated.				
74AUP1G00 v.3	20101007	Product data sheet	-	74AUP1G00 v.2		
74AUP1G00 v.2	20060629	Product data sheet	-	74AUP1G00 v.1		
74AUP1G00 v.1	20050711	Product data sheet	-	-		

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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